

AP50T10AGI-HF-VB Datasheet

N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY

| $V_{(BR)DSS}$ (V) | $r_{DS(on)}$ (Ω) | I_D (A) |
|-------------------|---------------------------|-----------------|
| 100 | 0.034 at $V_{GS} = 10$ V | 50 ^a |

FEATURES

- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 % R_g Tested

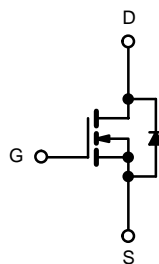
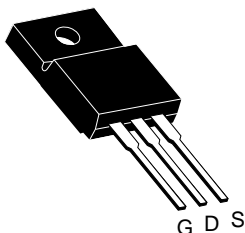


RoHS
COMPLIANT

APPLICATIONS

- Isolated DC/DC Converters

TO-220 FULLPAK



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

| Parameter | Symbol | Limit | Unit |
|--|----------------|------------------|------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current ($T_J = 175$ °C) | I_D | 50 ^a | A |
| | | 28 ^a | |
| Pulsed Drain Current | I_{DM} | 120 | |
| Avalanche Current | I_{AS} | 31 | |
| Single Pulse Avalanche Energy ^b | E_{AS} | 61 | mJ |
| Maximum Power Dissipation ^b | P_D | 360 ^c | W |
| | | 3.70 | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 175 | °C |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Limit | Unit |
|--------------------------|------------|-------|------|
| Junction-to-Ambient | R_{thJA} | 40 | °C/W |
| Junction-to-Case (Drain) | R_{thJC} | 0.4 | |

Notes:

a. Package limited.

b. Duty cycle ≤ 1 %.

c. See SOA curve for voltage derating.

d. When Mounted on 1" square PCB (FR-4 material).

| SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted | | | | | | |
|--|---------------|---|------|-------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 100 | | | V |
| Gate-Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 1.5 | | 2.5 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^{\circ}\text{C}$ | | | 50 | |
| | | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^{\circ}\text{C}$ | | | 250 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | 120 | | | A |
| Drain-Source On-State Resistance ^a | $r_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}$ | | 0.034 | | Ω |
| | | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$ | | 0.063 | | |
| | | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$ | | 0.084 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 30\text{ A}$ | 25 | | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 5100 | | pF |
| Output Capacitance | C_{oss} | | | 480 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 210 | | |
| Total Gate Charge ^c | Q_g | $V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 65\text{ A}$ | | 90 | 130 | nC |
| Gate-Source Charge ^c | Q_{gs} | | | 23 | | |
| Gate-Drain Charge ^c | Q_{gd} | | | 34 | | |
| Gate Resistance | R_g | | 0.5 | 1.7 | 3.3 | Ω |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = 100\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 65\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$ | | 24 | 35 | ns |
| Rise Time ^c | t_r | | | 220 | 330 | |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | | | 45 | 70 | |
| Fall Time ^c | t_f | | | 200 | 300 | |
| Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^{\circ}\text{C}$ ^b | | | | | | |
| Continuous Current | I_S | | | 50 | | A |
| Pulsed Current | I_{SM} | | | 120 | | |
| Forward Voltage ^a | V_{SD} | $I_F = 65\text{ A}, V_{GS} = 0\text{ V}$ | | 1.0 | 1.5 | V |
| Reverse Recovery Time | t_{rr} | $I_F = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 130 | 200 | ns |
| Peak Reverse Recovery Current | $I_{RM(REC)}$ | | | 8 | 12 | A |
| Reverse Recovery Charge | Q_{rr} | | | 0.52 | 1.2 | μC |

Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

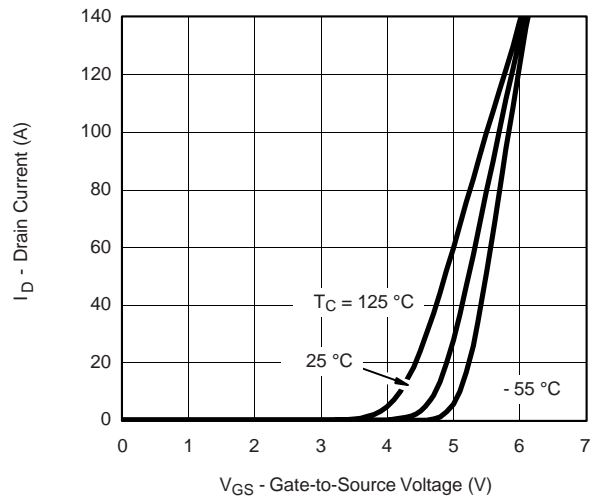
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



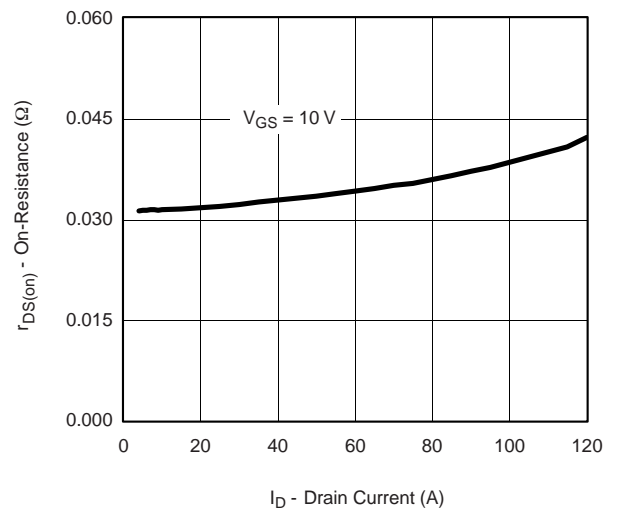
Output Characteristics



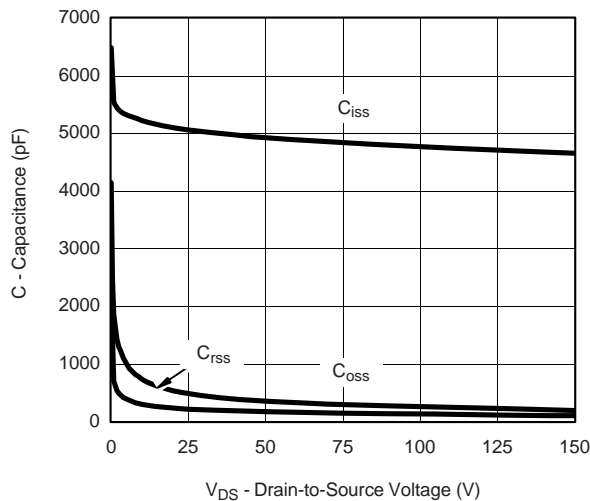
Transfer Characteristics



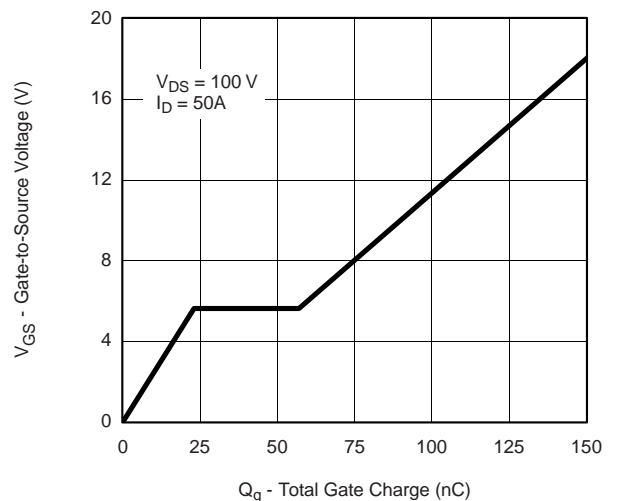
Transconductance



On-Resistance vs. Drain Current



Capacitance



Gate Charge

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



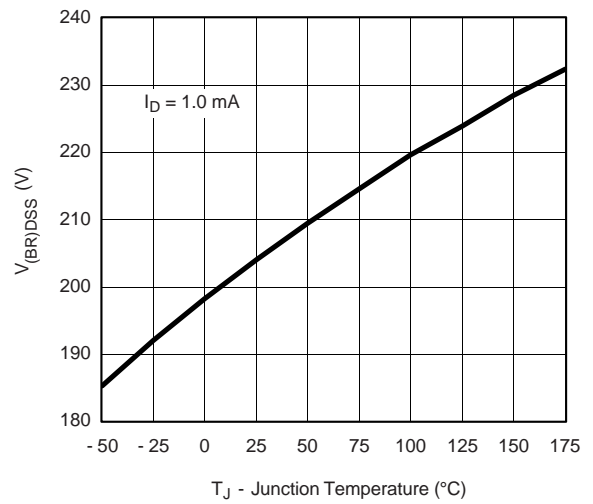
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



Avalanche Current vs. Time

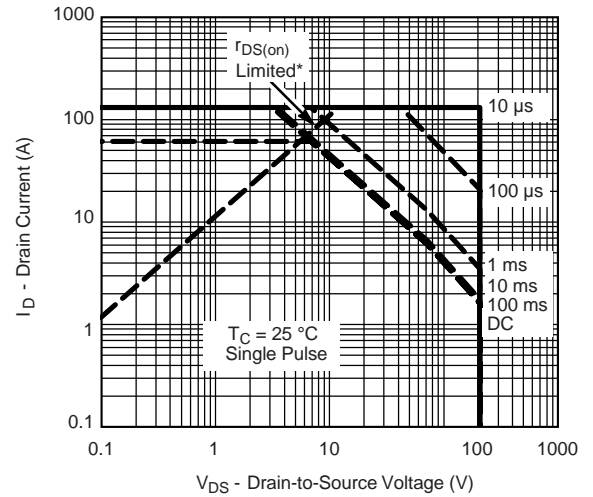


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS



**Maximum Avalanche and Drain Current
vs. Case Temperature**



* V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-220 FULLPAK (HIGH VOLTAGE)

| DIM. | MILLIMETERS | | INCHES | |
|------|-------------|--------|-----------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.570 | 4.830 | 0.180 | 0.190 |
| A1 | 2.570 | 2.830 | 0.101 | 0.111 |
| A2 | 2.510 | 2.850 | 0.099 | 0.112 |
| b | 0.622 | 0.890 | 0.024 | 0.035 |
| b2 | 1.229 | 1.400 | 0.048 | 0.055 |
| b3 | 1.229 | 1.400 | 0.048 | 0.055 |
| c | 0.440 | 0.629 | 0.017 | 0.025 |
| D | 8.650 | 9.800 | 0.341 | 0.386 |
| d1 | 15.88 | 16.120 | 0.622 | 0.635 |
| d3 | 12.300 | 12.920 | 0.484 | 0.509 |
| E | 10.360 | 10.630 | 0.408 | 0.419 |
| e | 2.54 BSC | | 0.100 BSC | |
| L | 13.200 | 13.730 | 0.520 | 0.541 |
| L1 | 3.100 | 3.500 | 0.122 | 0.138 |
| n | 6.050 | 6.150 | 0.238 | 0.242 |
| Ø P | 3.050 | 3.450 | 0.120 | 0.136 |
| u | 2.400 | 2.500 | 0.094 | 0.098 |
| v | 0.400 | 0.500 | 0.016 | 0.020 |

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DWG: 5972

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet $C_{pk} > 1.33$.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.

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